



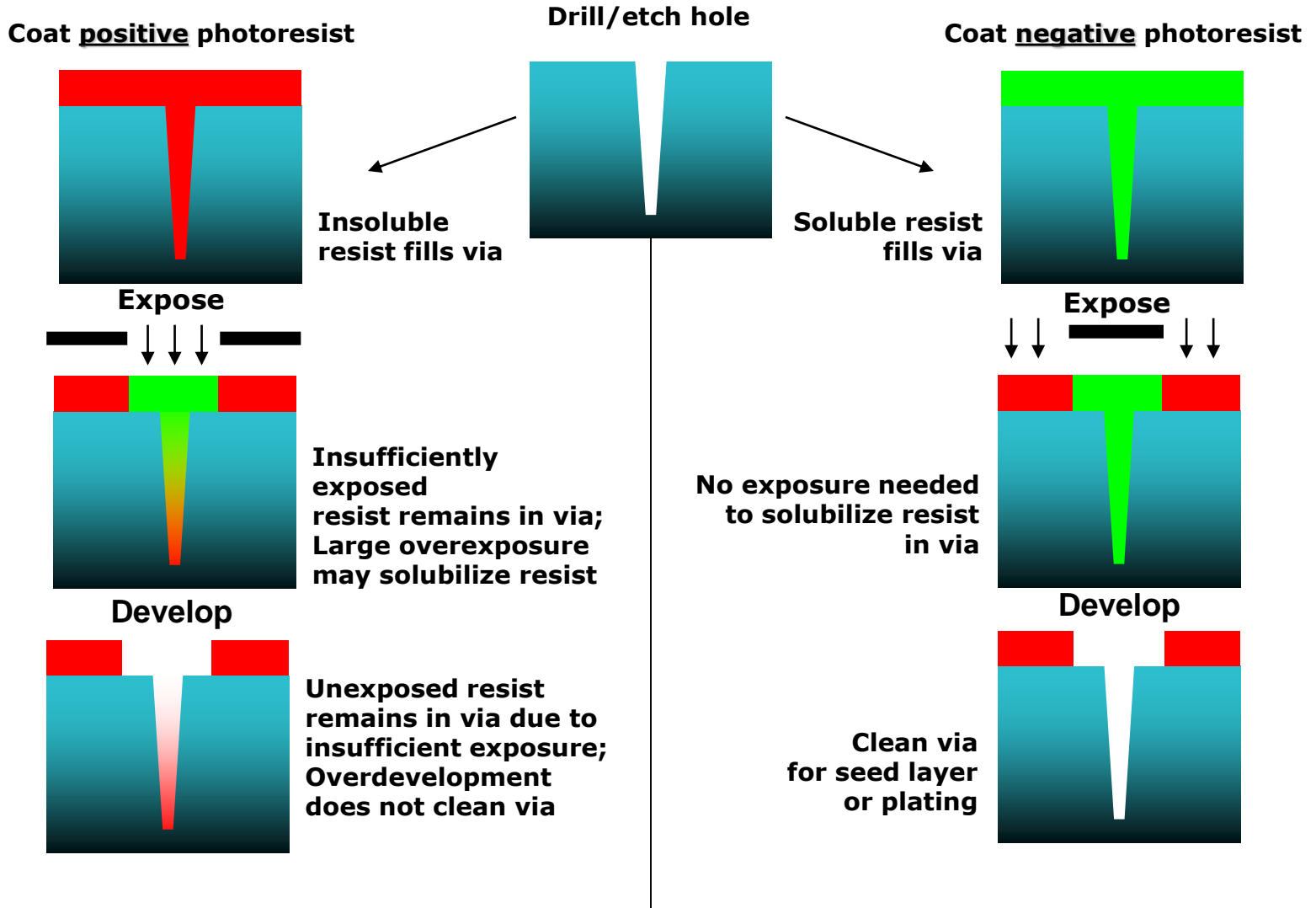
# **AZ<sup>®</sup> 15nXT (115 CPS) Photoresist**

**Negative Acting Thick Resist for  
Cu RDL, TSV, and other plating & etch applications  
Lithographic Performance Comparison at 6  $\mu$ m FT on Cu  
wafers**

October 2015

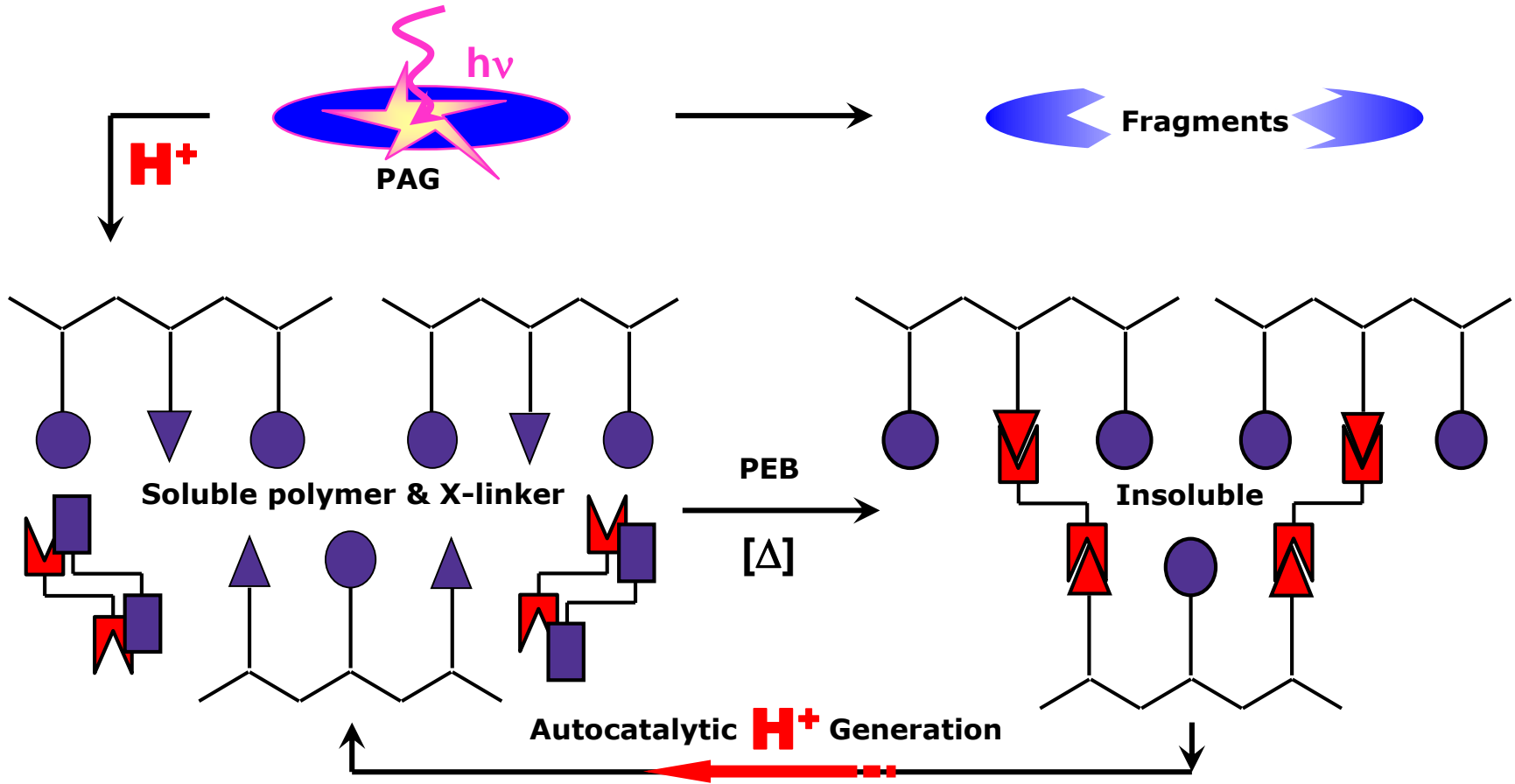
**MERCK**

# Through-Silicon-Via (TSV) Advantages to Use a Negative Photoresist



# Chemically Amplified Negative Resist

The original photo-event generates a catalyst for crosslinking (typically a proton). The photo-event is amplified by the number of cycles each proton catalyzes.



## AZ® 15nXT (115 CPS) Process Conditions

Substrate:	Si wafer for photospeed testing Cu wafer for images
Film Thickness:	6 µm by single coat
Softbake:	110°C / 120 seconds
Exposure tool:	ASML (i-line) Dose = $300 \pm 50$ mJ/cm <sup>2</sup> ; Focus: $1 \pm 0.5$ µm
PEB:	120°C / 60 seconds
Develop:	AZ 300 MIF (2.38% TMAH); 2 x 55 second puddles

## AZ® 15nXT (115 CPS) Optical Parameters

n & k Values at different wavelength

365 nm:     n = 1.6807   k = 0.0027

633 nm:     n = 1.6063   k = 0.0034

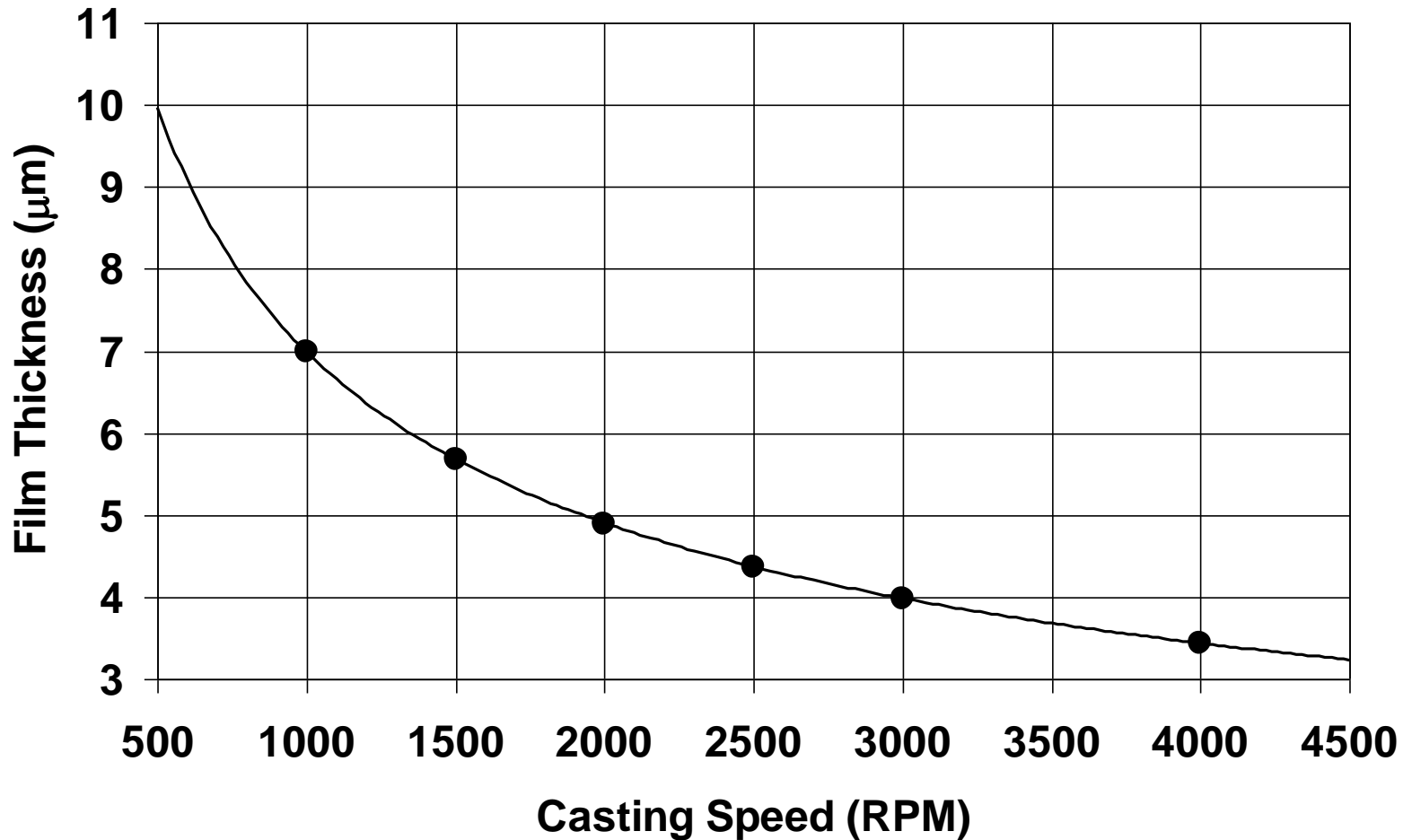
Cauchy coefficients (A, B, C) fit the following Cauchy equation:  $n = A + B/\lambda^2 + C/\lambda^4$

A = 1.5754

B = 0.013242 mm<sup>2</sup>

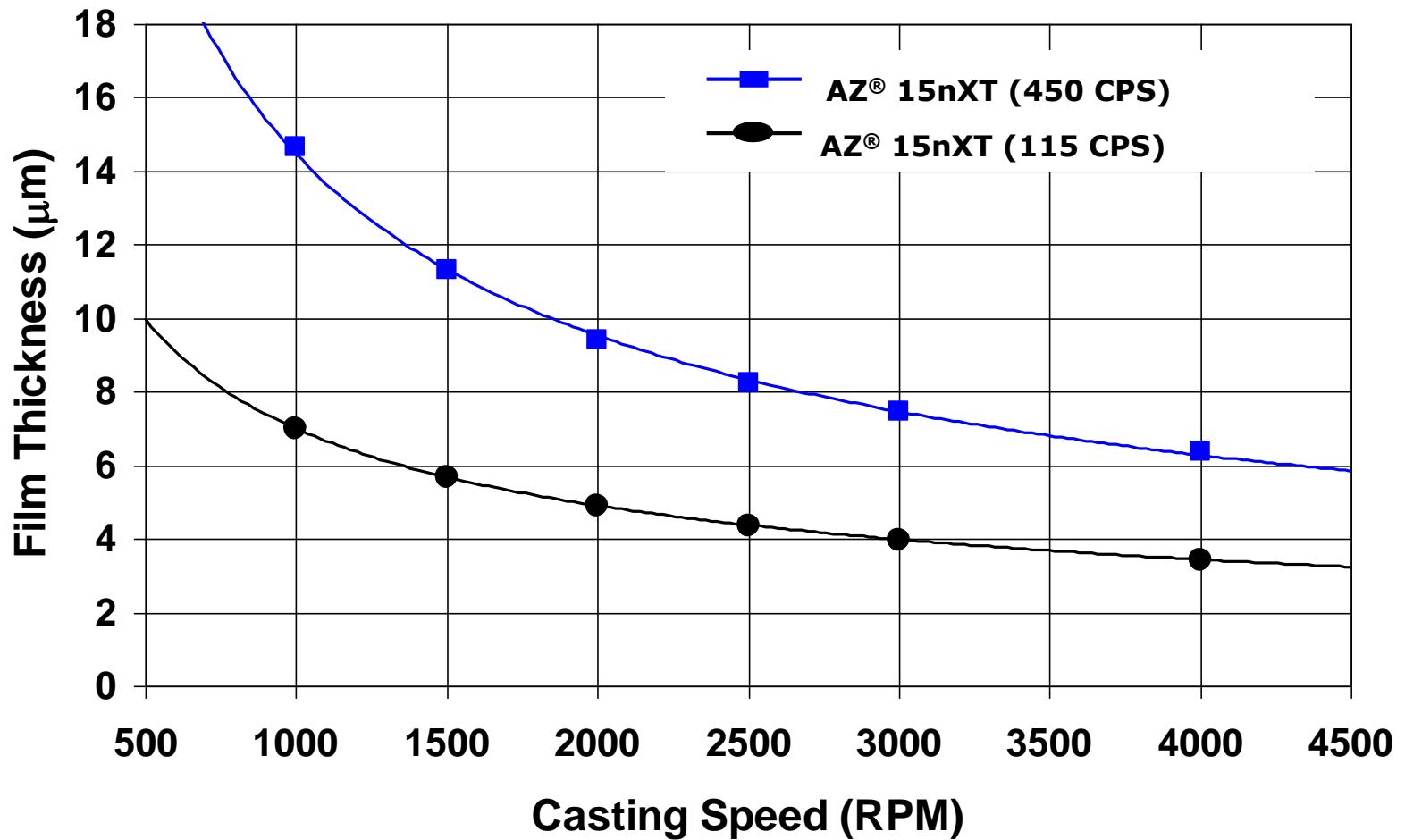
C = 0 mm<sup>4</sup>

## AZ<sup>®</sup> 15nXT (115 CPS) Spin Speed Curve



Opti-Trak Coat and Bake  
Hand dispense on 150 mm silicon  
Spin 1000-4000 rpm for 30 sec  
SB: 110°C/ 2 minutes

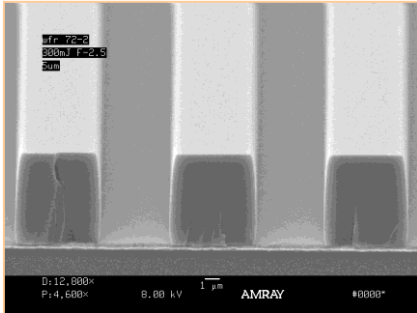
## AZ<sup>®</sup> 15nXT (115 CPS) and AZ<sup>®</sup> 15nXT (450 CPS) Spin Speed Curves



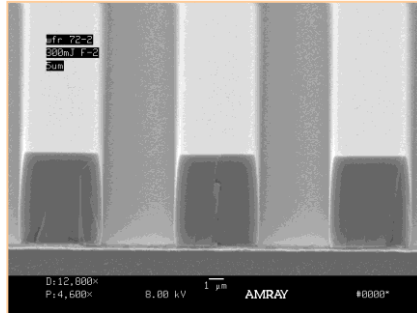
Opti-Trak Coat and Bake  
Hand dispense on 150 mm silicon  
Spin 1000-4000 rpm for 30 sec  
SB: 110°C/ 3 min for 15nXT  
110°C/2 min for 5nXT

# AZ<sup>®</sup> 15nXT (115 CPS) DOF on Cu Wafer @ 300 mJ/cm<sup>2</sup>

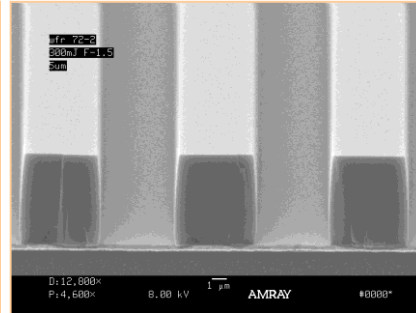
f -2.5



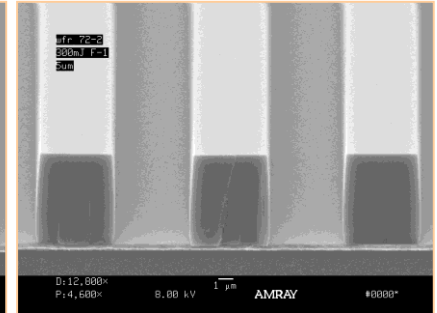
f -2.0



f -1.5

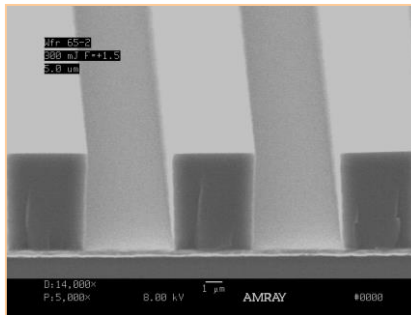
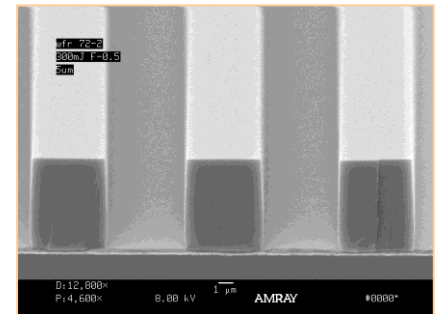


f -1.0

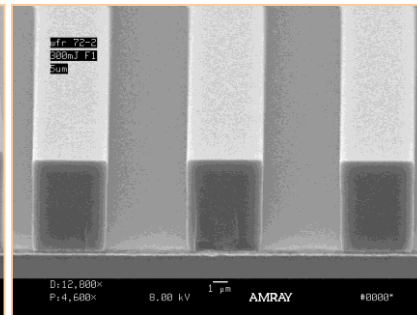


Film Thickness: 6.0mm  
Opti Track Coat and Bake  
SB: 110°C/2 minutes  
ASML i-Line Stepper, 300mJ/cm<sup>2</sup>  
Opti Track PEB/Develop  
PEB: 120°C/ 60 Seconds  
AZ 300 MIF/ 2x55sec Spray/Puddle @23°C

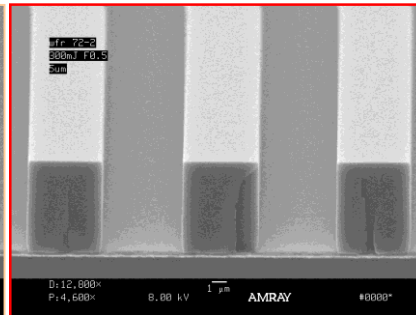
f -0.5



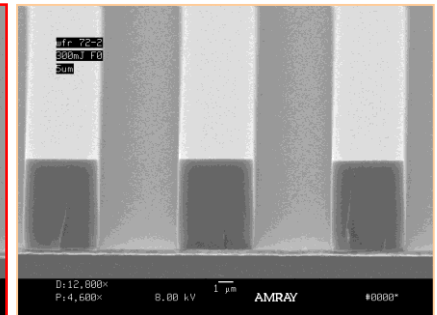
f +1.5



f +1.0



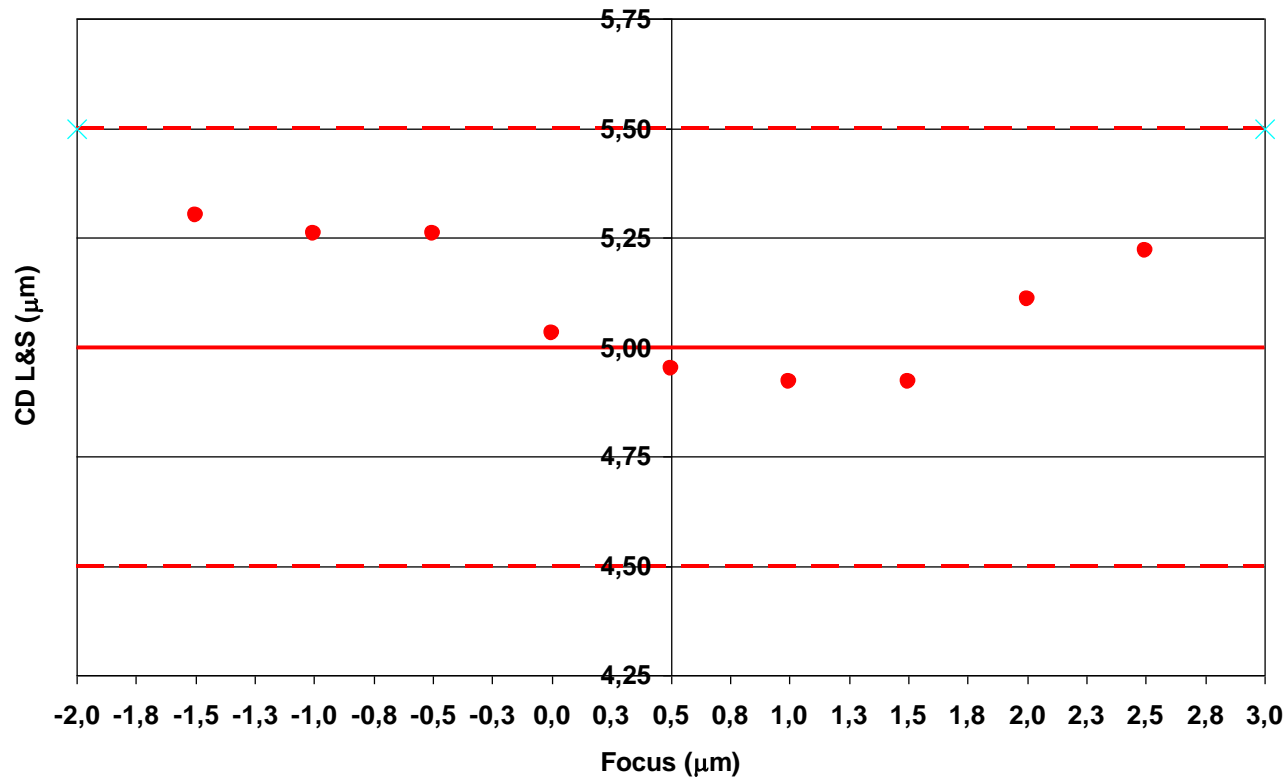
f +0.5



f 0.0

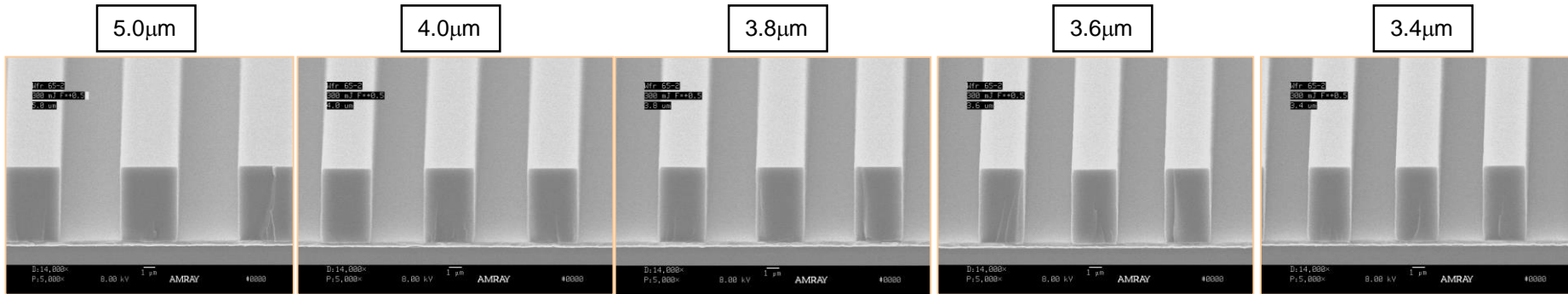


# AZ® 15nXT (115 CPS) DOF on Cu Wafer @ 300 mJ/cm<sup>2</sup>

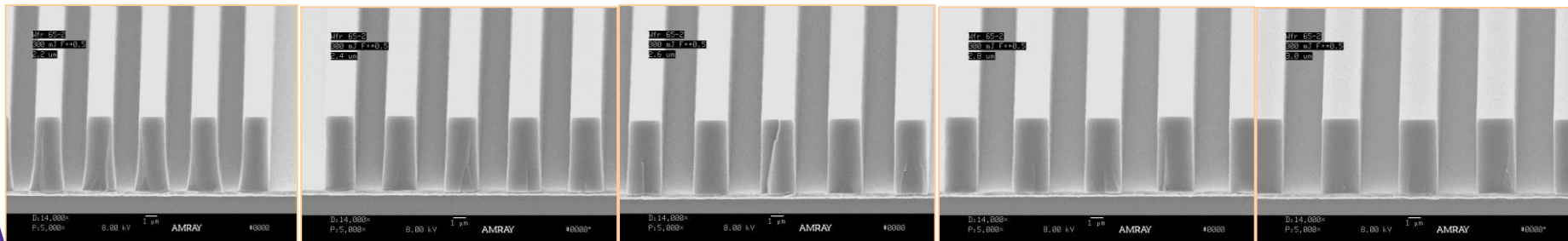
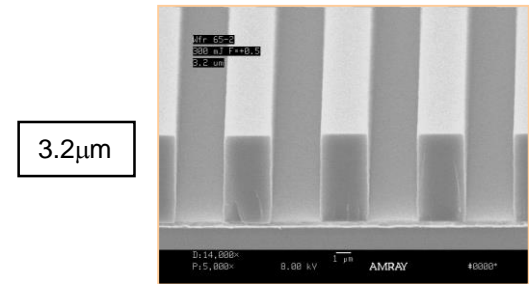


Film Thickness: 6.0mm  
Opti Track Coat and Bake  
SB: 110°C/2 minutes  
ASML i-Line Stepper, 300mJ/cm<sup>2</sup>  
Opti Track PEB/Develop  
PEB: 120°C/ 60 Seconds  
AZ 300 MIF/ 2x55sec Spray/Puddle @23°C

# AZ<sup>®</sup> 15nXT (115 CPS) Linearity @ 300 mJ/cm<sup>2</sup>, F= + 0.5 mm



Film Thickness: 6.0mm  
Opti Track Coat and Bake  
SB: 110°C/2 minutes  
ASML i-Line Stepper, F= +0.5mm  
Opti Track PEB/Develop  
PEB: 120°C/ 60 Seconds  
AZ 300 MIF/ 2x55sec Spray/Puddle @23°C



# AZ<sup>®</sup> 15nXT (115 CPS) Exposure Latitude @ F = 0.5 mm, FT = 6.0 mm, 5 mm L/S

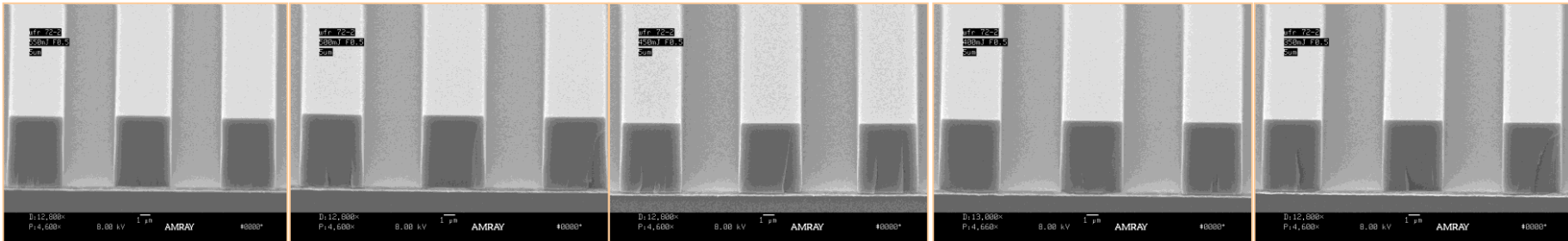
550 mJ/cm<sup>2</sup>

500 mJ/cm<sup>2</sup>

450 mJ/cm<sup>2</sup>

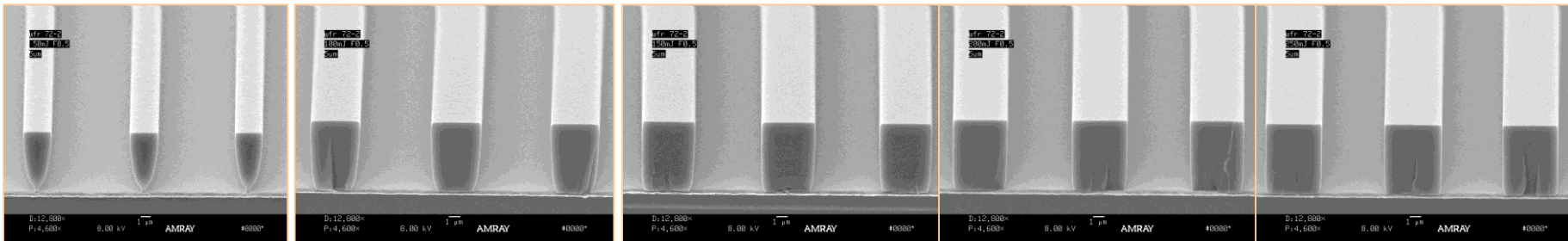
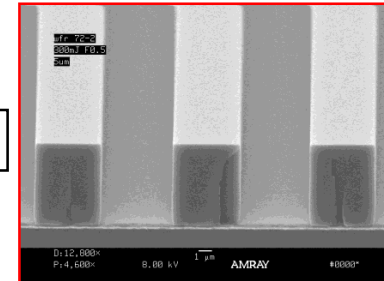
400 mJ/cm<sup>2</sup>

350 mJ/cm<sup>2</sup>



Film Thickness: 6.0mm  
Opti Track Coat and Bake  
SB: 110°C/2 minutes  
ASML i-Line Stepper, F= +0.5mm  
Opti Track PEB/Develop  
PEB: 120°C/ 60 Seconds  
Chill: 21°C/120 Seconds  
AZ 300 MIF/ 2x55sec Spray/Puddle @23°C

300 mJ/cm<sup>2</sup>



50 mJ/cm<sup>2</sup>

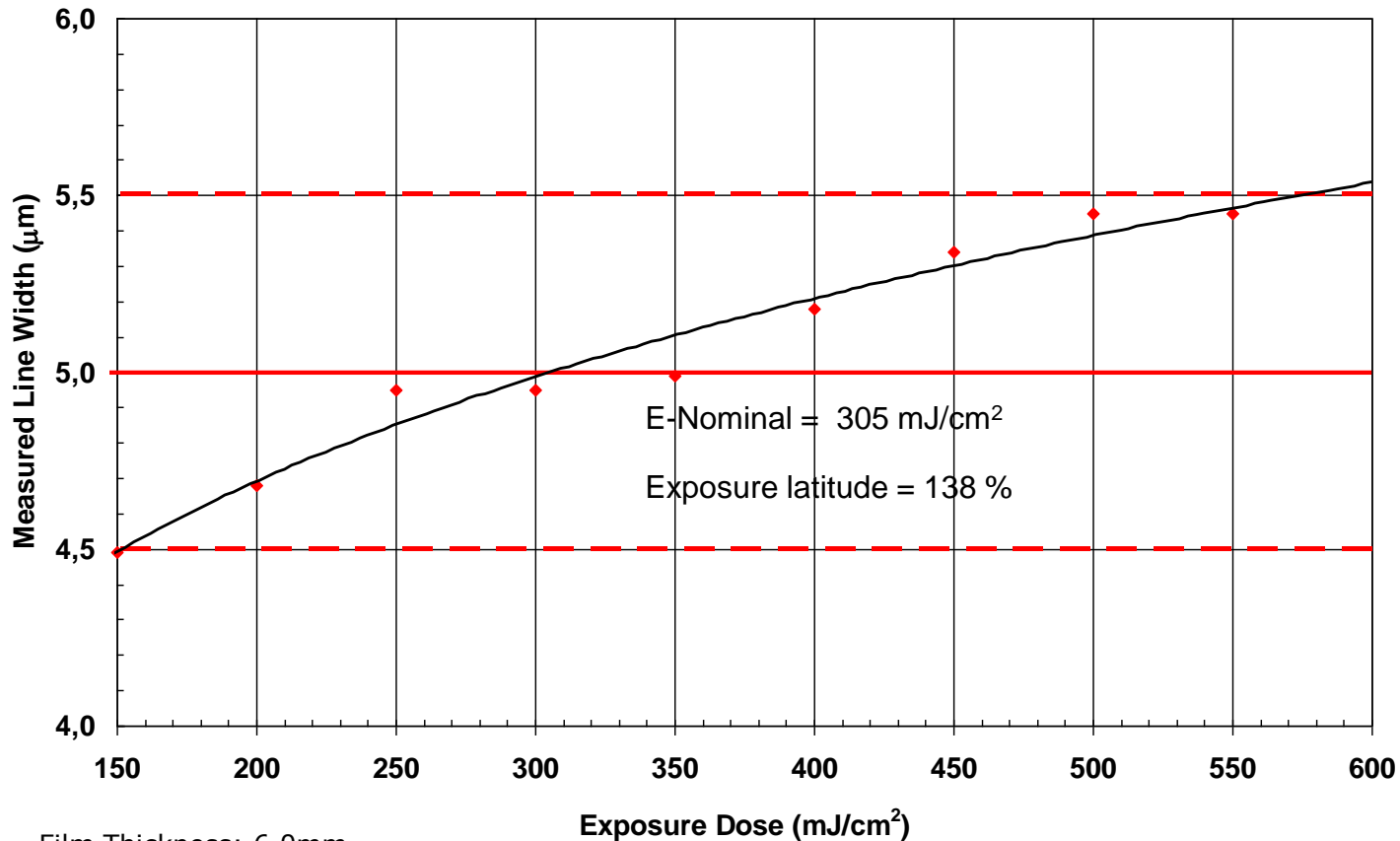
100 mJ/cm<sup>2</sup>

150 mJ/cm<sup>2</sup>

200 mJ/cm<sup>2</sup>

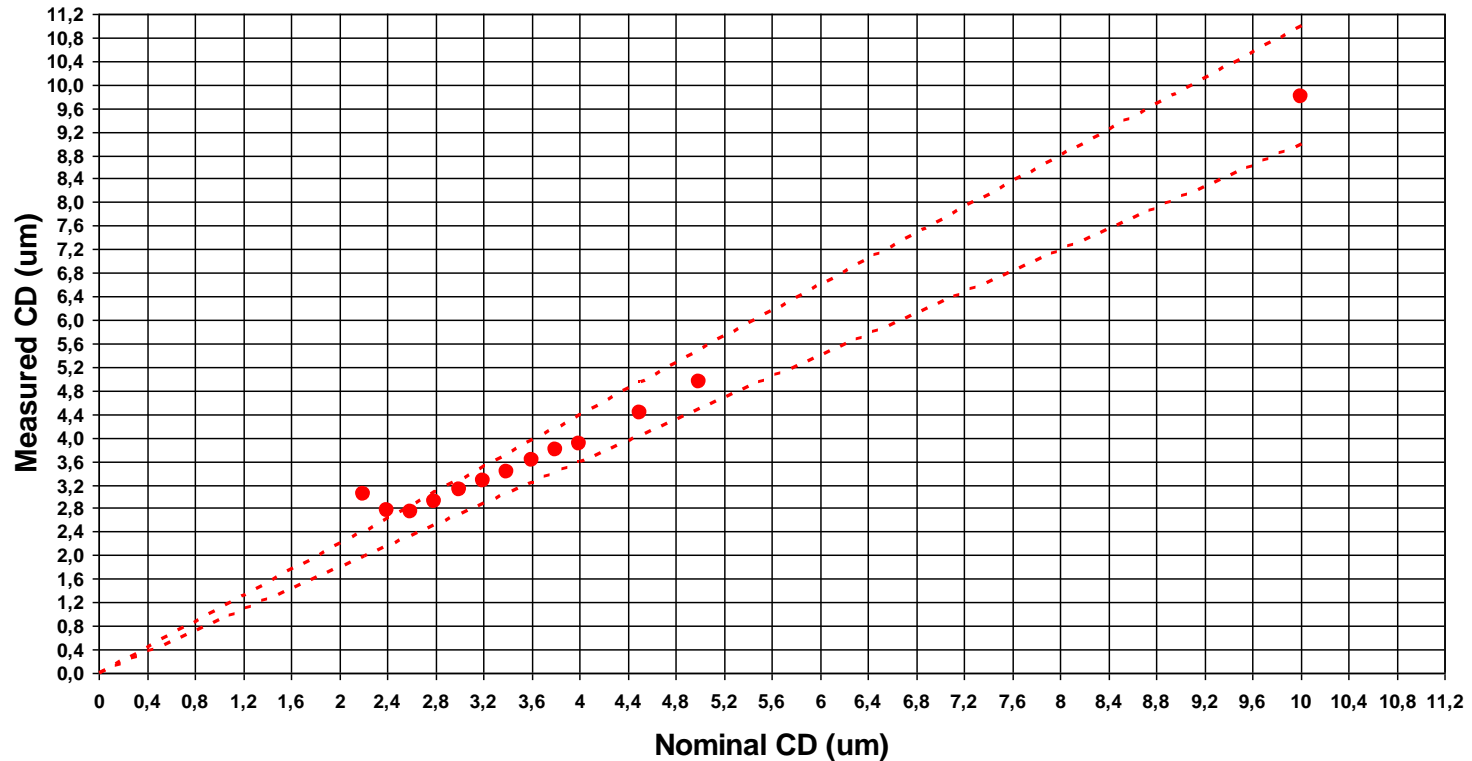
250 mJ/cm<sup>2</sup>

# AZ<sup>®</sup> 15nXT (115 CPS) FT = 6.0 mm, Focus = +0.5 mm 5.0 mm L/S Exposure Latitude on Cu Wafer



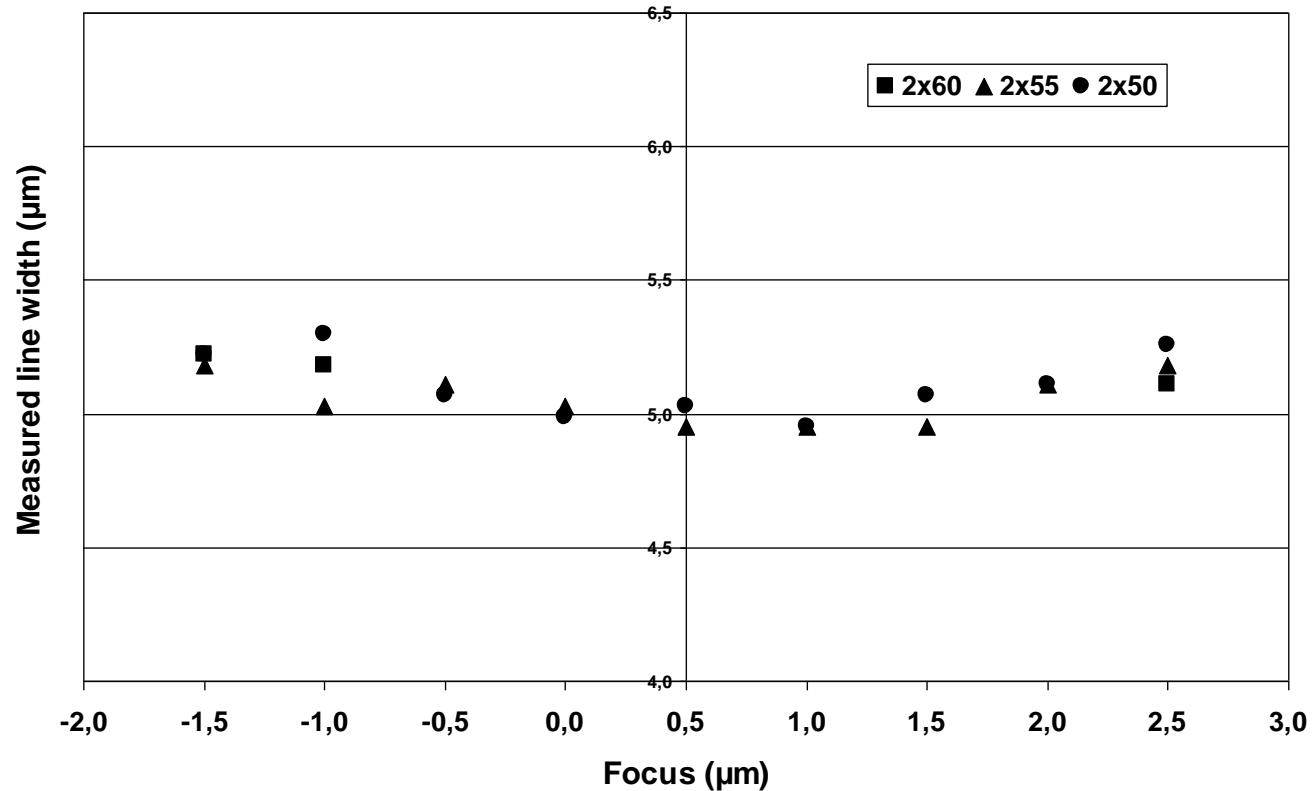
Film Thickness: 6.0mm  
Opti Track Coat and Bake  
SB: 110°C/2 minutes  
ASML i-Line Stepper, F= +0.5mm  
Opti Track PEB/Develop  
PEB: 120°C/ 60 Seconds  
AZ 300 MIF/ 2x55sec Spray/Puddle @23°C

# AZ<sup>®</sup> 15nXT (115 CPS) L/S Linearity @ 300 mJ/cm<sup>2</sup>, F = +0.5 mm



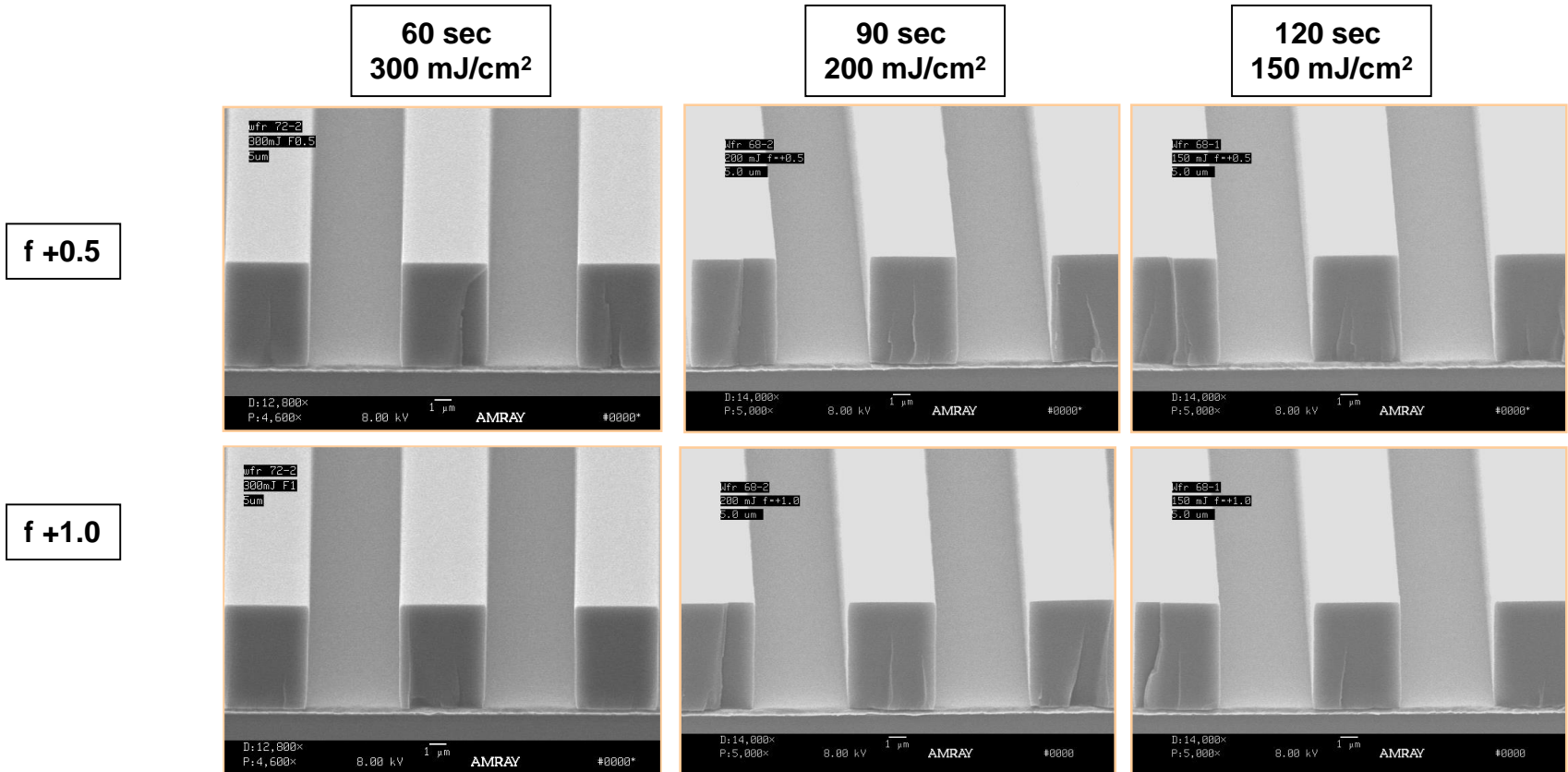
Film Thickness: 6.0mm  
Opti Track Coat and Bake  
SB: 110°C/2 minutes  
ASML i-Line Stepper, F= +0.5mm  
Opti Track PEB/Develop  
PEB: 120°C/ 60 Seconds  
AZ 300 MIF/ 2x55sec Spray/Puddle @23°C

# AZ<sup>®</sup> 15nXT (115 CPS) FT = 6.0 mm, 5.0 mm L/S Development Window on Cu Wafer



Film Thickness: 6.0mm  
Opti Track Coat and Bake  
SB: 110°C/2 minutes  
ASML i-Line Stepper, 250 mJ/cm<sup>2</sup>  
Opti Track PEB/Develop  
PEB: 120°C/ 60 Seconds  
AZ 300 MIF/ 2x55sec Spray/Puddle @23°C

# AZ<sup>®</sup> 15nXT (115 CPS) PEB Comparison on Cu Wafers @ 6 mm FT



Opti Track Coat and Bake  
 SB: 110°C/2 minutes  
 Film Thickness: 6.0mm/ 5.0mm L&S  
 ASML i-Line Stepper  
 Opti Track PEB/Develop  
 PEB: 120°C/ 60, 90, 120 Seconds  
 Chill: 21°C/120 Seconds  
 AZ 300 MIF/ 2x55sec Spray/Puddle @23°C

## AZ® 15nXT (115 CPS) Summary

- Compatible on Cu type substrates and other metals.
- Very good lithographic throughput; very competitive photospeed and develop time.
- Excellent adhesion, no underplating.
- Vertical sidewall profiles.
- Wide compatibility to plating solutions, including Cu, Ni, and Au.
- Easily strips after plating; stripped completely in AZ Kwik Strip at 70°C for 3 min.
- Very good stability and shelf life
- Thicker version available for higher FT range; 15nXT (450 CPS).